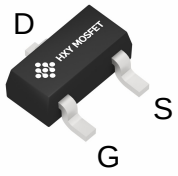
HXY5P04MI

P-Channel Enhancement Mode MOSFET

Description

The HXY5P04MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V.
This device is suitable for use as a Battery protection or in other Switching application.



SOT-23-3L

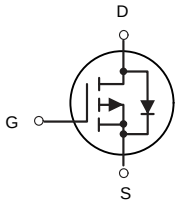
General Features

V_{DS} = -40V,I_D = -5A

$R_{DS(ON)}$ < 54mΩ @ V_{GS}=10V

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY5P04MI	SOT-23-3L	5P04	3000PCS

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	-5	A
I_{DM}	Drain Current-Pulsed (Note 1)	-22	A
P_D	Maximum Power Dissipation	2	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	65	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -40V, V_{GS}=0V	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note2	V_{GS}= -10V, I_D= -5A	-	45	54	mΩ
		V_{GS}= -4.5V, I_D= -4A	-	60	85	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -20V, V_{GS}=0V, f=1.0MHz	-	869	-	pF
C_{oss}	Output Capacitance		-	94	-	pF
C_{rss}	Reverse Transfer Capacitance		-	69	-	pF
Q_g	Total Gate Charge	V_{DS}= -20V, I_D= -4A, V_{GS}= -10V	-	17.3	-	nC
Q_{gs}	Gate-Source Charge		-	3.2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	4.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}= -20V, I_D= -4A, V_{GS}= -10V, R_{GEN}=3Ω	-	10.3	-	ns
t_r	Turn-on Rise Time		-	4.3	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	39	-	ns
t_f	Turn-off Fall Time		-	46.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5.0	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-22	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -5.5A	-	-0.8	-1.2	V
trr	Reverse Recovery Time	V_{GS}=0V, I_S= -5.5A, di/dt=100A/μs	-	17	-	ns
Qrr	Reverse Recovery Charge		-	11.5	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

Figure1: Output Characteristics

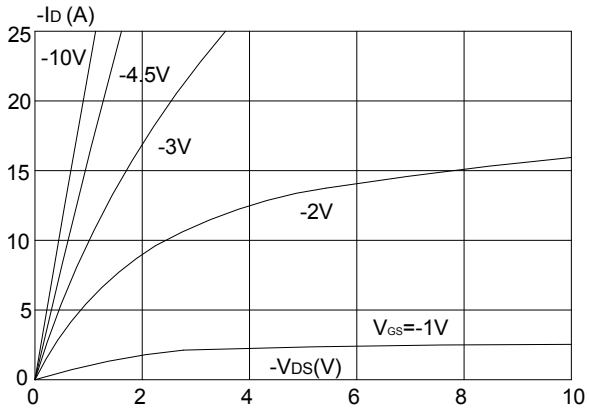


Figure 2: Typical Transfer Characteristics

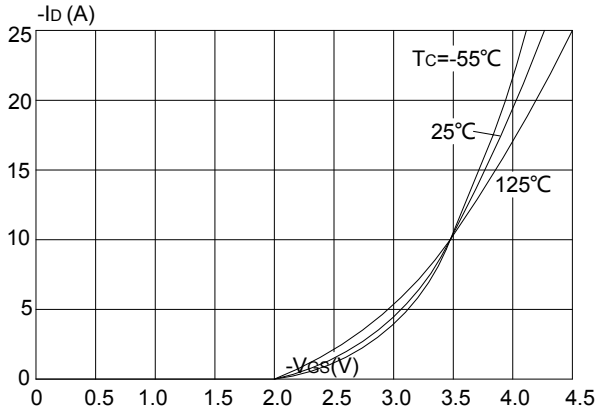


Figure 3: On-resistance vs. Drain Current

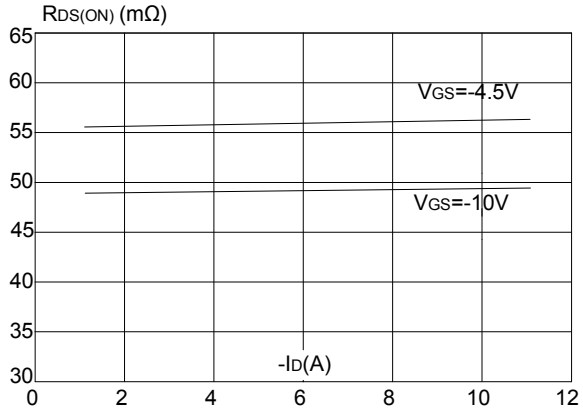


Figure 4: Body Diode Characteristics

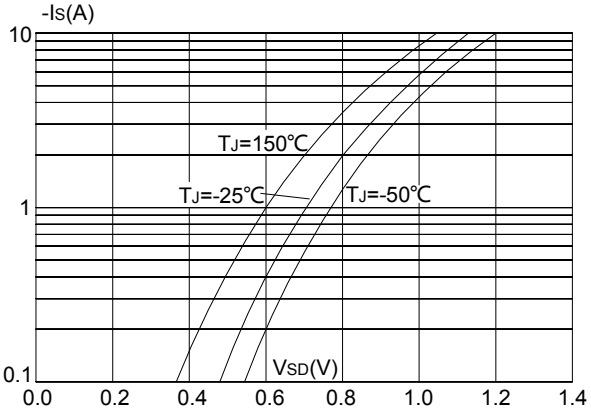


Figure 5: Gate Charge Characteristics

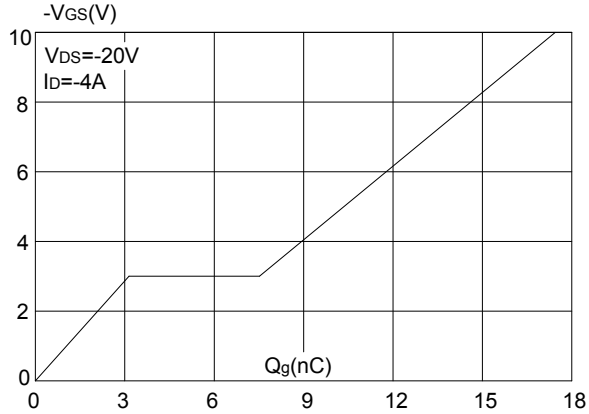


Figure 6: Capacitance Characteristics

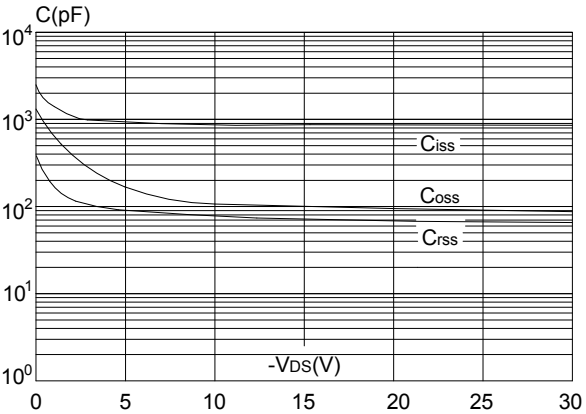


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

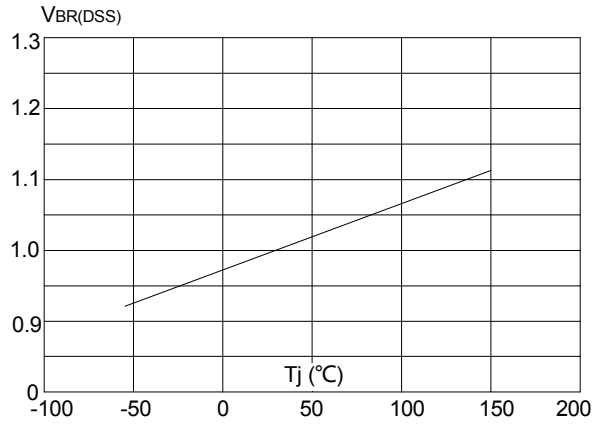


Figure 8: Normalized on Resistance vs. Junction Temperature

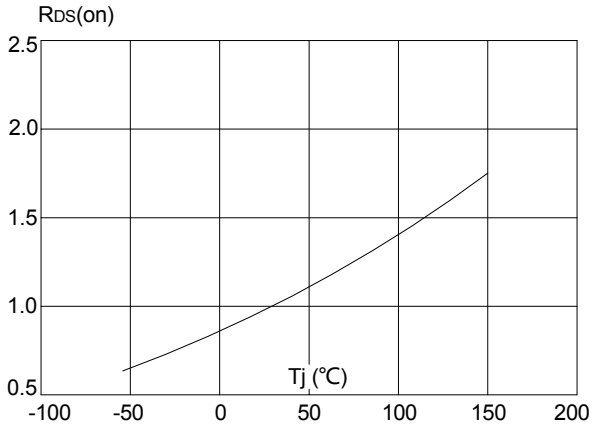


Figure 9: Maximum Safe Operating Area

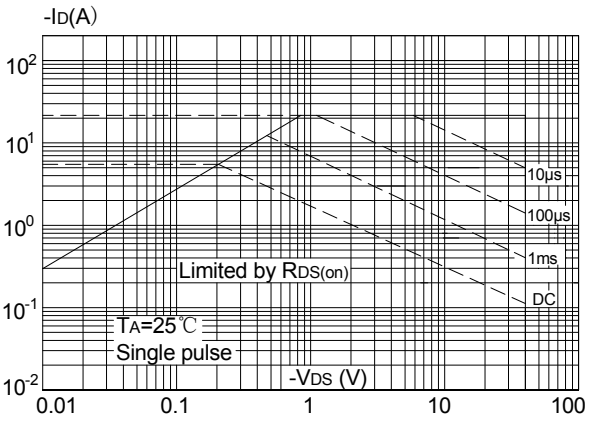


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

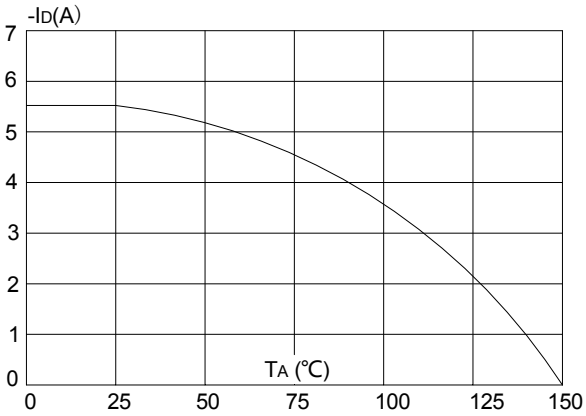
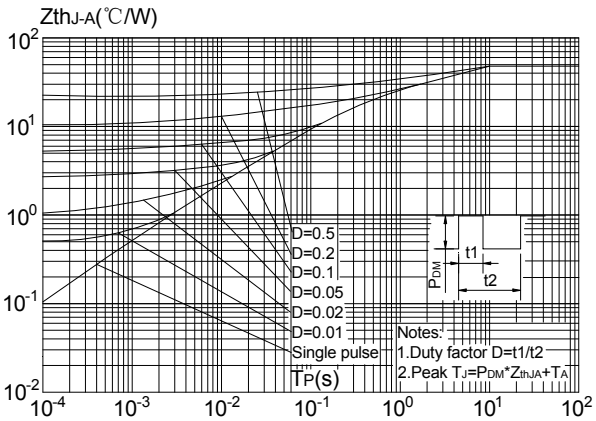
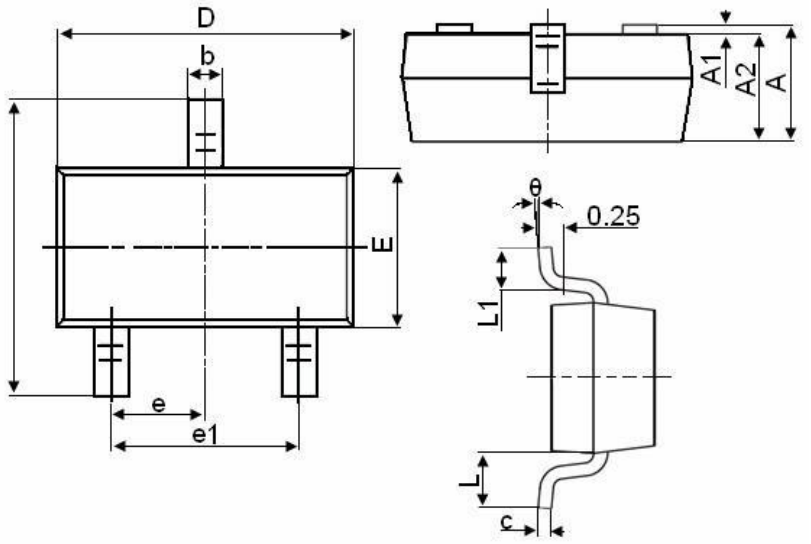


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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